

## NSBC114YPDP6T5G

#### **NSBC114YPDP6T5G Information**

www.netvener.com	 NSBC114YPDP6T5G ON Semiconductor Discrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-Biased TRANS NPN/PNP PREBIAS SOT963 SOT-963 For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

#### **Certified Quality**

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### NSBC114YPDP6T5G Specifications

Manufacturer Part Number NSBC114YPDP6T5G   Manufacturer ON Semiconductor   Category Discrete Semiconductor Products   Transistors - Bipolar (BJT) - Arrays, Pre-Biased Transistors - Bipolar (BJT) - Arrays, Pre-Biased   Package SOT-963   Series -   Transistor Type 1 NPN, 1 PNP - Pre-Biased (Dual)   Current - Collector (Lc) (Max) 100mA   Voltage - Collector Emitter Breakdown (Max) 50V   Resistor - Base (R1) (Ohms) 10k   Resistor - Emitter Base (R2) (Ohms) 47k   DC Current Gain (hFE) (Min) @ Lc, Vce 80 @ 5mA, 10V   Vec Saturation (Max) @ Ib, Lc 500nA   Current - Collector Cutoff (Max) 500nA   Frequency - Transition -   Prequency - Transition -   Power - Max 339mW   Mounting Type SOT-963   Supplicr Device Package SOT-963		
CategoryDiscrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lo) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Lc, Vce80 @ 5mA, 10VVes Saturation (Max) @ Jb, Lc500nACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Manufacturer Part Number	NSBC114YPDP6T5G
IntegryTransistors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lc) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Lc, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Lc250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Manufacturer	ON Semiconductor
PackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Base (R2) (Ohms)47kDC Current Gain (hFE) (Min @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Category	Discrete Semiconductor Products
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Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lo (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Lc, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Lc250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Package	SOT-963
Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Series	-
Voltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max33mWMounting TypeSurface MountPackage / CaseS0T-963Supplier Device PackageS0T-963	Transistor Type	1 NPN, 1 PNP - Pre-Biased (Dual)
Resistor - Base (R1) (Ohms)10kResistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Current - Collector (Ic) (Max)	100mA
Resistor - Emitter Base (R2) (Ohms)47kDC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Voltage - Collector Emitter Breakdown (Max)	50V
DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Resistor - Base (R1) (Ohms)	10k
Vce Saturation (Max) @ Ib, Ic250mV @ 300µA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Resistor - Emitter Base (R2) (Ohms)	47k
Current - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	DC Current Gain (hFE) (Min) @ Ic, Vce	80 @ 5mA, 10V
Frequency - Transition-Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Vce Saturation (Max) @ Ib, Ic	250mV @ 300µA, 10mA
Power - Max339mWMounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Current - Collector Cutoff (Max)	500nA
Mounting TypeSurface MountPackage / CaseSOT-963Supplier Device PackageSOT-963	Frequency - Transition	_
Package / CaseSOT-963Supplier Device PackageSOT-963	Power - Max	339mW
Supplier Device Package SOT-963	Mounting Type	Surface Mount
	Package / Case	SOT-963
Report errors?	Supplier Device Package	SOT-963
		Report errors?

#### NSBC114YPDP6T5G Guarantees



**Quality Guarantees** 

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

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#### **Service Guarantees**

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

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